

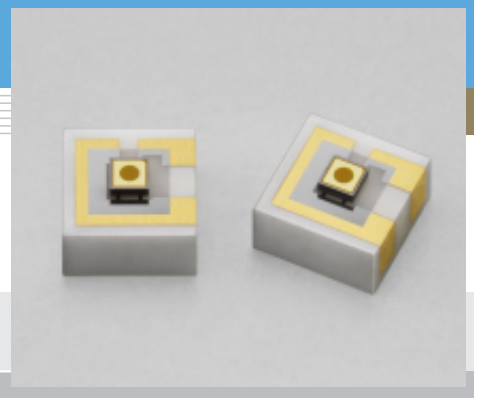
NEW

PHOTODIODE

InGaAs PIN photodiode

G9230-01

Uses small package with no wire



Features

- Easy to handle since there are no wires on chip (AnSn eutectic bonding)
Optical fibers can be brought closer to the chip
- Miniature package: 2 × 2 × 1 mm
- High sensitivity: 0.95 A/W Typ. ($\lambda=1.55 \mu\text{m}$)
- Precise chip position tolerance: $\pm 0.075 \text{ mm}$

Applications

- LD monitor
- Optical fiber communication

■ General / Absolute maximum ratings

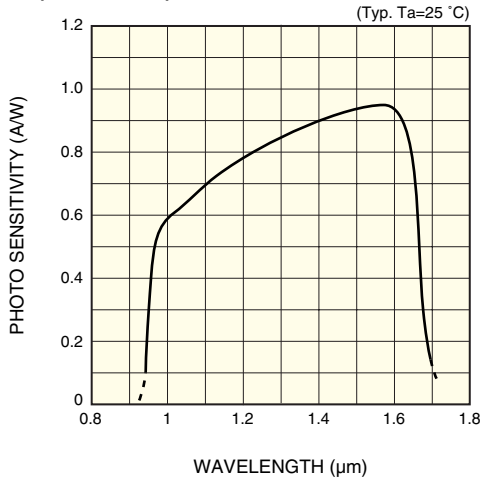
| Parameter | Symbol | value | Unit |
|-------------------------|------------|------------|------|
| Active area | - | $\phi 0.3$ | mm |
| Reverse voltage | V_R Max. | 10 | V |
| Operating temperature * | Topr. | -40 to +85 | °C |
| Storage temperature * | Tstg. | -40 to +85 | °C |

* In N₂ environment or in vacuum

■ Electrical and optical characteristics (Ta=25 °C)

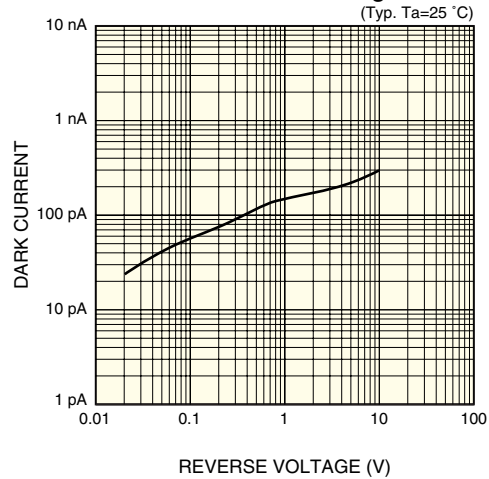
| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|-------------------------|-----------|------------------------------------|------|---------------------|------|---------------------|
| Spectral response range | λ | | - | 0.95 to 1.7 | - | μm |
| Photo sensitivity | S | $\lambda=1.3 \mu\text{m}$ | - | 0.85 | - | A/W |
| | | $\lambda=1.55 \mu\text{m}$ | 0.85 | 0.95 | - | A/W |
| Dark current | I_D | $V_R=5 \text{ V}$ | - | 0.3 | 1.5 | nA |
| Shunt resistance | Rsh | $V_R=10 \text{ mV}$ | - | 1000 | - | M Ω |
| Terminal capacitance | Ct | $V_R=5 \text{ V}, f=1 \text{ MHz}$ | - | 5 | - | pF |
| Cut-off frequency | fc | $V_R=5 \text{ V}, R_L=50 \Omega$ | - | 400 | - | MHz |
| Noise equivalent power | NEP | $\lambda=\lambda_p$ | - | 4×10^{-15} | - | W/Hz ^{1/2} |

■ Spectral response



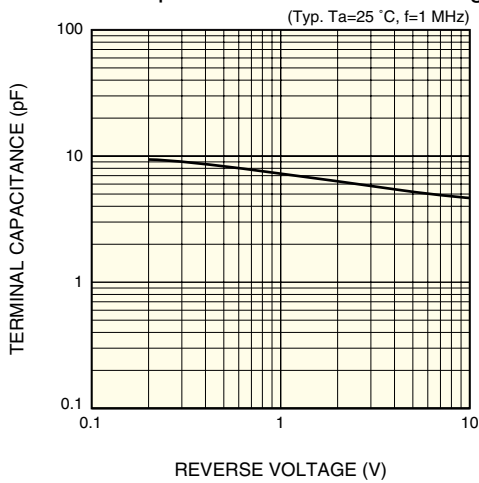
KIRD0287EA

■ Dark current vs. reverse voltage



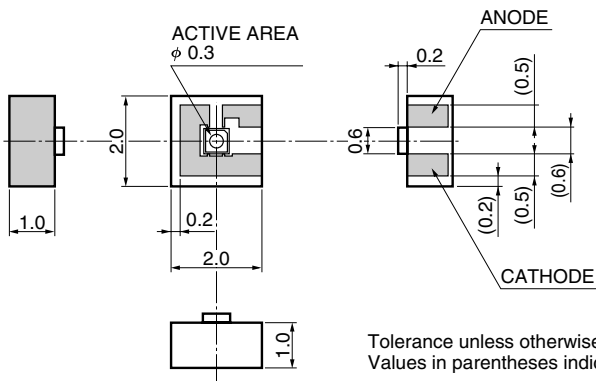
KIRD0288EA

■ Terminal capacitance vs. reverse voltage



KIRD0289EA

■ Dimensional outline (unit: mm)



KIRDA0168EA

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